

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1694517	(non near volatile) memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:29
S2	19056	S1 and (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:30
S3	8921	S2 and (isolat\$3 (field near oxide) ST1 LOCOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:32
S4	8020	S3 and (gate (word near line\$1) BL)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:33
S5	8052	S3 and (gate (word near line\$1) (bit near line\$1) BL)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:34
S6	1002	S5 and (charge near trap\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 14:34
S7	289	S6 and (active near (region\$1 area\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 15:47
S8	10	("5663084" "5751037" "6023085" "6074915" "6087211" "6130168" "6197639" "6204159" "6436768" "6468865").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 15:28
S9	1	S6 and (substrate with ((cell memory) near (region\$1 area\$1)) with ((high near voltage) near (region\$1 area\$1)) with ((low near voltage) near (region\$1 area\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 15:51

S10	12	S2 and (substrate with ((cell memory) near (region\$1 area\$1)) with ((high near voltage) near (region\$1 area\$1)) with ((low near voltage) near (region\$1 area\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 15:53
S11	33	S2 and (((cell memory) near (region\$1 area\$1)) with ((high near voltage) near (region\$1 area\$1)) with ((low near voltage) near (region\$1 area\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/22 15:53
S12	13	("4471373" "5104819" "5188976" "5409854" "5472892" "5514889" "5856221" "5861347" "5888869" "6121116" "6133093" "6159799" "6165846").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/22 15:58